ETR0212-004a

### Voltage Detector with Delay Circuit Built-In

#### **■**GENERAL DESCRIPTION

The XC61H series is a highly accurate, low power consumption CMOS voltage detector with a delay circuit. Detect voltage is accurate with minimal temperature drift. Output configurations are available in both CMOS and N-channel open drain. Since the full delay circuit is built-in, an external delay-time capacitor is not necessary so that high density mounting is possible.

#### APPLICATIONS

- Microprocessor reset circuitry
- System battery life and charge voltage monitors
- Memory battery back-up circuits
- Power-on reset circuits
- Power failure detection
- Delay circuitry

#### **■**FEATURES

**Detect Voltage Accuracy** : ± 2%

**Low Power Consumption** :  $1.0 \,\mu$  A(TYP.)[  $V_{IN}=2.0V$  ] **Detect Voltage Range** : 1.6V ~ 6.0V (0.1V increments)

**Operating Voltage Range** : 0.7V ~ 10.0V **Detect Voltage Temperature Characteristics** 

: ±100ppm/°C(TYP.)

Built-In Release Delay time: 1ms (MIN.)

50ms (MIN.) 80ms (MIN.)

**Output Configuration** : N-ch open drain output or CMOS

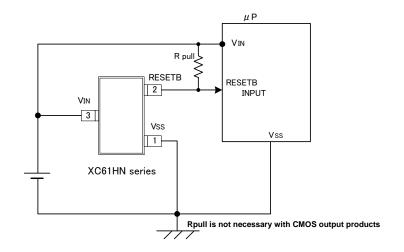
Operating Ambient Temperature : -30°C~80°C **Package** : SOT-23

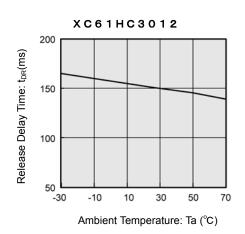
Environmentally Friendly : EU RoHS Compliant, Pb Free

## ■TYPICAL APPLICATION CIRCUITS ■TYPICAL PERFORMANCE

# CHARACTERISTICS

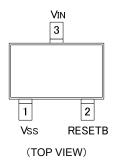
● Release Delay Time (t<sub>DR</sub>) vs. Ambient Temperature





#### **■ PIN CONFIGURATION**

#### **■PIN ASSIGNMENT**



PIN NUMBER	PIN NAME	FUNCTION		
SOT-23	PIN INAIVIE	FUNCTION		
1	V <sub>SS</sub> Ground			
2	RESETB	Output		
3	$V_{IN}$	Supply Voltage Input		

### **■PRODUCT CLASSIFICATION**

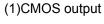
Ordering Information

XC61H1)234567-8(\*1)

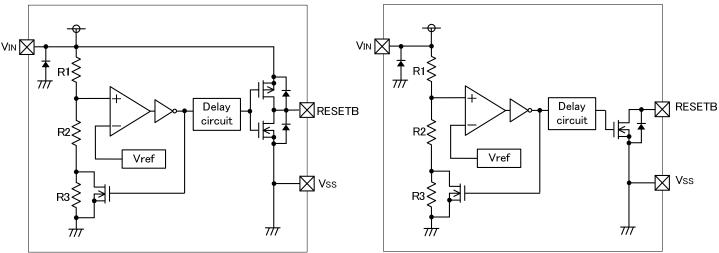
DESIGNATOR	ITEM	SYMBOL	DESCRIPTION	
	Output Configuration	С	CMOS output	
1		N	N-ch open drain output	
23	Detect Voltage (VDF)	16 ~ 60	e.g. 2.5V → ②2, ③5	
		1	50ms ~ 200ms	
4	Release Delay Time	4	80ms ~ 400ms	
		5	1ms ~ 50ms	
5	Detect Accuracy	2	± 2.0%(*2)	
<b>6</b> 7- <b>8</b> (*1)	Package (Oder Unit)	MR-G	SOT-23 (3000pcs/Reel)	

<sup>(\*1)</sup> The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

### **■BLOCK DIAGRAMS**



#### (2)N-ch open drain output



<sup>(\*2)</sup> No parts are available with an accuracy of  $\pm$  1%

## ■ ABSOLUTE MAXIMUM RATINGS

Ta=25°C

PARAMETER		SYMBOL	RATINGS	UNITS	
Input Voltage		$V_{IN}$	V <sub>SS</sub> -0.3 ~ 12.0	V	
Output Current		Іоит	50	mA	
Output Voltage	CMOS	\/	V <sub>SS</sub> -0.3 ~V <sub>IN</sub> +0.3	V	
	N-ch open drain output	V <sub>RESETB</sub>	V <sub>SS</sub> -0.3 ~ 12		
Power Dissipation SOT-23		Pd	250	mW	
Operating Ambient Temperature		Topr	-30~+80	သိ	
Storage Temperature		Tstg	-40~+125	°C	

### **■**ELECTRICAL CHARACTERISTICS

Ta = 25°C

PARA	AMETER	SYMBOL	CONDITIO	ONS	MIN.	TYP.	MAX.	UNITS	CIRCUIT
Detec	ct Voltage	$V_{DF}$			V <sub>DF(T)</sub> x 0.98	$V_{DF(T)}$	V <sub>DF(T)</sub> x 1.02	<b>&gt;</b>	1
Hyster	esis Width	V <sub>HYS</sub>			V <sub>DF</sub> x 0.02	V <sub>DF</sub> x 0.05	V <sub>DF</sub> x 0.08	V	1
				V <sub>IN</sub> = 1.5V	-	0.9	2.6		
				V <sub>IN</sub> = 2.0V	ı	1.0	3.0		
Supply	Current (*1)	Iss		V <sub>IN</sub> = 3.0V	-	1.3	3.4	μΑ	2
				$V_{IN} = 4.0V$	-	1.6	3.8	]	
				$V_{IN} = 5.0V$	-	2.0	4.2		
Operati	ing Voltage	V <sub>IN</sub>	V <sub>DF</sub> =1.6V∼6.0V		0.7	-	10.0	V	1
		Іоит	N-ch, V <sub>DS</sub> = 0.5V	V <sub>IN</sub> = 1.0V	1.0	2.2	-	mA	3
				$V_{IN} = 2.0V$	3.0	7.7	-		
				V <sub>IN</sub> = 3.0V	5.0	10.1	-		
Outpu	ıt Current			V <sub>IN</sub> = 4.0V	6.0	11.5	-		
				V <sub>IN</sub> = 5.0V	7.0	13.0	-		
			P-ch, V <sub>DS</sub> =2.1V (CMOS Output)	V <sub>IN</sub> = 8.0V		-10.0	-2.0		4
Leakage	CMOS Output (Pch)	I <sub>LEAK</sub>	V <sub>IN</sub> =V <sub>DF</sub> x 0.9V, V <sub>RESETB</sub> =0V		-	-0.01	-	μΑ	3
Current	Nch Open Drain Output		V <sub>IN</sub> =10.0V, V <sub>RESETB</sub> =10.0V		-	0.01	0.1		
			-	±100	-	ppm/°C	1		
Release	Release Delay Time		VIN changes from 0.6V to 10V		50	-	200	ms	5
	(VDR → RESETB inversion)				80	-	400		
(VDR / NESETB IIIVersion)					1	-	50		

VDF (T) is nominal detect voltage value Release Voltage: VDR = VDF + VHYS

<sup>(\*1)</sup> The supply current during power-start until output being stable (during release operation) is 2  $\mu$  A greater with comparison to the period after the completion of release operation because of the shoot-through current in delay current.

#### ■ OPERATIONAL EXPLANATION

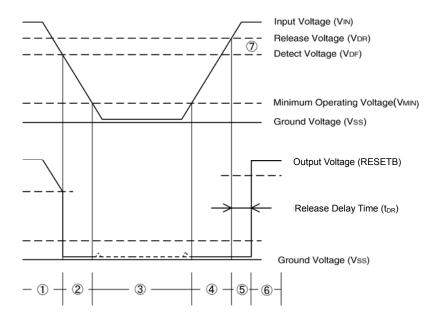
#### CMOS output

- ① An input voltage V<sub>IN</sub> starts higher than the release voltage V<sub>DR</sub>. Then, V<sub>IN</sub> voltage will gradually fall. When V<sub>IN</sub> voltage is higher than detect voltage V<sub>DF</sub>, output voltage RESETB is equal to the V<sub>IN</sub> voltage.
  - \*Note that high impedance exists at RESETB with the N-channel open drain output configuration. If the RESETB pin is pulled up, RESETB will be equal to the pull up voltage.
- ② When VIN falls below VDF, RESETB will be equal to ground voltage Vss level (detect state).
  - \* Note that this also applies to N-channel open drain output configurations.
- When VIN falls to a level below that of the minimum operating voltage VMIN, output will become unstable.
  \*When the output pin is generally pulled up with N-channel open drain output configurations, output will be equal to pull up voltage.
- When Vin rises above the Vss level (excepting levels lower than minimum operating voltage), RESETB will be equal to Vss until Vin reaches the VDR level.
- S Although Vin will rise to a level higher than VDR, RESETB maintains ground voltage level via the delay circuit.
- After taking a release delay time, VIN voltage will be output at the RESETB pin.
   \*High impedance exists with the N-channel open drain output configuration and that voltage will be dependent on pull up.

#### Notes:

- 1. The difference between VDR and VDF represents the hysteresis width.
- 2. Release delay time ( $t_{DR}$ ) represents the time it takes until when VIN voltage appears at RESETB pin once the input voltage has exceeded the VDR level.

#### Timing Chart



#### ■NOTES ON USE

- 1. Please use this IC within the stated maximum ratings. For temporary, transitional voltage drop or voltage rising phenomenon, the IC is liable to malfunction should the ratings be exceeded.
- 2. When a resistor is connected between the V<sub>IN</sub> pin and the power supply with CMOS output configurations, irregular oscillation may occur as a result of voltage drops at R<sub>IN</sub> if load current (I<sub>OUT</sub>) exists. It is therefore recommend that no resistor be added. (refer to Figure 1 below)
- 3. When a resistor (R<sub>IN</sub>) is connected between the V<sub>IN</sub> pin and the power supply with CMOS output configurations, irrespective of N-ch open drain output configurations, oscillation may occur as a result of shoot-through current at the time of voltage release even if load current (I<sub>OUT</sub>) does not exist. (refer to Figure 2 below)
- 4. If a resistor (R<sub>IN</sub>) must be used, then please use with as small a level of input impedance as possible in order to control the occurrences of oscillation as described above. Further, please ensure that R<sub>IN</sub> is less than 10kΩ and that C<sub>IN</sub> is more than 0.1 μF, please test with the actual device. However, N-ch open drain output only. (Figure 1).
- 5. With a resistor RIN connected between the VIN pin and the power supply, the VIN pin voltage will be getting lower than the power supply voltage as a result of the IC's supply current flowing through the VIN pin.
- 6. Depending on circuit's operation, release delay time of this IC can be widely changed due to upper limits or lower limits of operational ambient temperature.
- 7. Torex places an importance on improving our products and its reliability.

  However, by any possibility, we would request user fail-safe design and post-aging treatment on system or equipment.

#### Irregular Oscillations

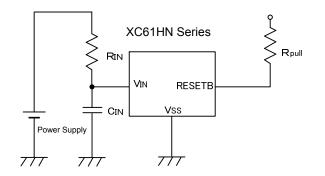
(1) Irregular oscillation as a result of load current with the CMOS output configuration:

When the voltage applied at power supply, release operations commence and the detector's output voltage increases. Load current ( $I_{OUT}$ ) will flow through  $R_L$ . Because a voltage drop ( $R_{IN} \times I_{OUT}$ ) is produced at the  $R_{IN}$  resistor, located between the power supply and the  $V_{IN}$  pin, the load current will flow via the IC's  $V_{IN}$  pin. The voltage drop will also lead to a fall in the voltage level at the  $V_{IN}$  pin. When the  $V_{IN}$  pin voltage level falls below the detect voltage level, detect operations will commence. Following detect operations, load current flow will cease and since voltage drop at  $R_{IN}$  will disappear, the voltage level at the  $V_{IN}$  pin will rise and release operations will begin over again. Irregular oscillation may occur with this "release - detect - release" repetition.

Further, this condition will also appear via means of a similar mechanism during detect operations.

(2) Irregular oscillation as a result of shoot-through current:

Since the XC61H series are CMOS ICs, shoot-through current will flow when the IC's internal circuit switching operates (during release and detect operations). Consequently, irregular oscillation is liable to occur during release voltage operations as a result of output current which is influenced by this shoot-through current (Figure 3). Since hysteresis exists during detect operations, irregular oscillation is unlikely to occur.



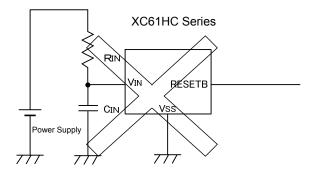


Figure 1 Use of input resistor RIN

## ■NOTES ON USE (Continued)

Irregular Oscillations (Continued)

#### XC61HC Series

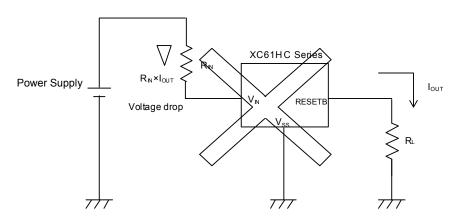


Figure 2 Irregular Oscillation by output current

## XC61HC Series XC61HN Series

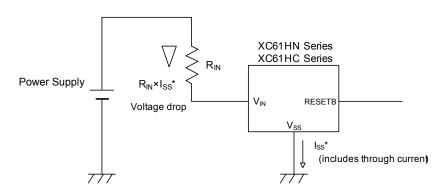
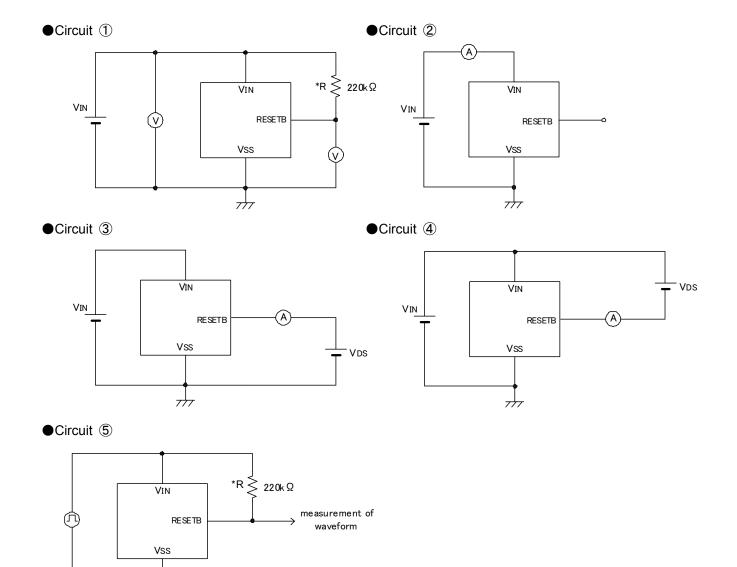


Figure 3 Irregular Oscillation by shoot-through current

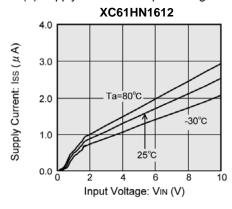
## **■**TEST CIRCUITS

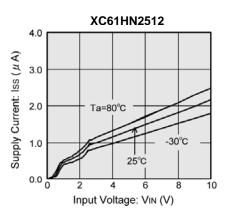


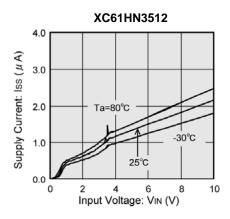
\*R is not necessary with CMOS output products.

#### **■**TYPICAL PERFORMANCE CHARACTERISTICS

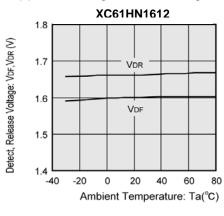
#### (1) Supply Current vs. Input Voltage

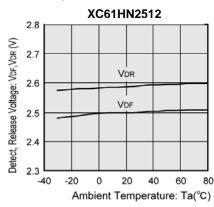


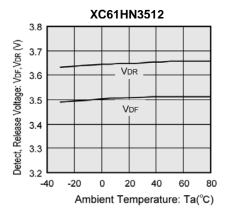




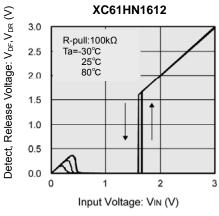
(2) Detect Voltage, Release Voltage vs. Ambient Temperature

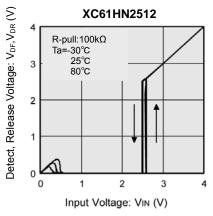


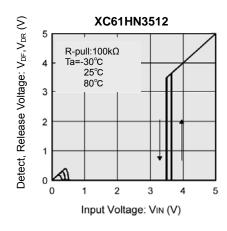




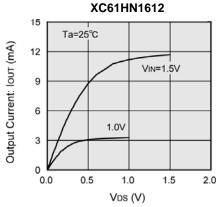
(3) Detect Voltage, Release Voltage vs. Input Voltage

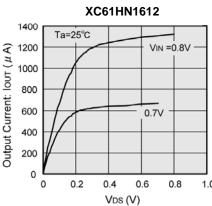


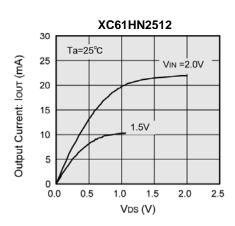




(4) N-Channel Driver Output Current vs. VDS

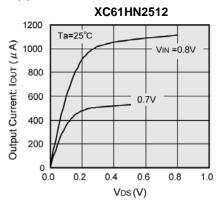


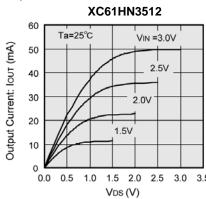


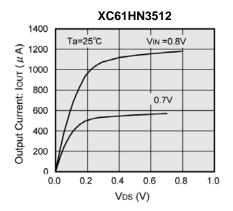


## ■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

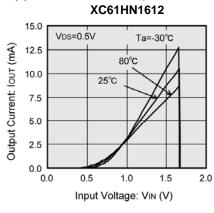
(4) N-Channel Driver Output Current vs. VDS (Continued)

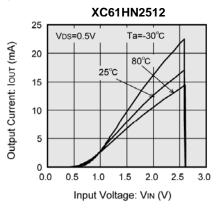


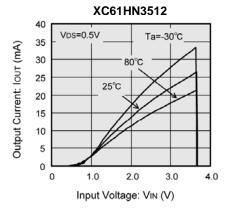




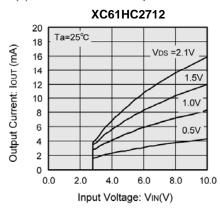
(5) N-Channel Driver Output Current vs. Input Voltage

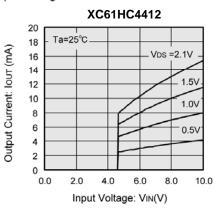




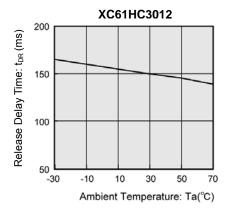


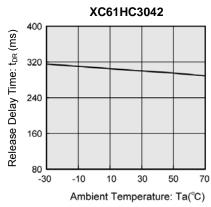
(6) P-Channel Driver Output Current vs. Input Voltage

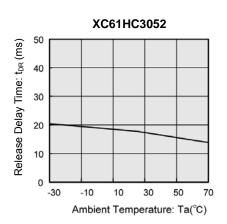




(7) Ambient Temperature vs. Release Delay Time (t<sub>DR</sub>)



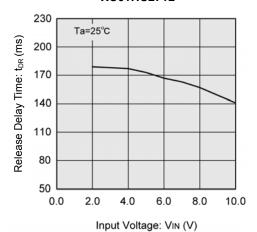




## ■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(8) Input Voltage vs. Release Delay Time  $(t_{DR})$ 

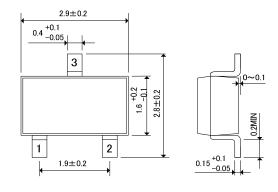
#### XC61HC2712



## ■ PACKAGING INFORMATION

#### ●SOT-23

(unit:mm)

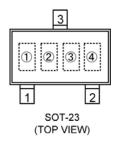




## XC61H Series

### **■**MARKING RULE

#### ●SOT-23



① represents product series

MARK	PRODUCTS SERIES
8	XC61H*****-G

2 standard : represents output configuration and integer number of detect voltage

CMOS output (XC61HC series)

MARK	VOLTAGE (V)	
Α	1. X	
В	2. X	
С	3. X	
D	4. X	
E	5. X	
F	6. X	

N-channel open drain (XC61HN series)

MARK	VOLTAGE (V)	
Р	1. X	
R	2. X	
S	3. X	
T	4. X	
U	5. X	
V	6. X	

③ represents decimal number of detect voltage and delay time.

DETECT	MARK					
VOLTAGE (V)	DELAY TIME 50ms~200ms (XC61H***1***-G)	DELAY TIME 80ms~400ms (XC61H***4***-G)	DELAY TIME 1ms~50ms (XC61H***5***-G)			
X.0	0	Α	N			
X.1	1	В	Р			
X.2	2	С	R			
X.3	3	D	S			
X.4	4	E	Т			
X.5	5	F	U			
X.6	6	Н	V			
X.7	7	K	X			
X.8	8	L	Y			
X.9	9	M	Z			

4 represents production lot number

0 to 9, A to Z or inverted characters of 0 to 9, A to Z repeated.

(G, I, J, O, Q,W excluded)

\*No character inversion used.

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